

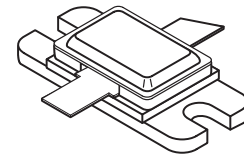
The RF Line Microwave Pulse Power Transistor

Designed for 1025–1150 MHz pulse common base amplifier applications such as TCAS, TACAN and Mode–S transmitters.

- Guaranteed Performance @ 1090 MHz
Output Power = 350 Watts Peak
Gain = 8.5 dB Min, 9.0 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Package
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input and Output Matching
- Characterized using Mode–S Pulse Format

MRF10350

**350 W (PEAK)
1025–1150 MHz
MICROWAVE POWER
TRANSISTOR
NPN SILICON**



CASE 355E–01, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CES}	65	Vdc
Collector–Base Voltage	V_{CBO}	65	Vdc
Emitter–Base Voltage	V_{EBO}	3.5	Vdc
Collector Current — Peak (1)	I_C	31	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ (1), (2) Derate above 25°C	P_D	1590 9.1	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	–65 to +200	$^\circ\text{C}$
Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	$R_{\theta JC}$	0.11	$^\circ\text{C}/\text{W}$

NOTES:

1. Under pulse RF operating conditions.
2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst Case θ_{JC} measured using Mode–S pulse train, 128 μs burst 0.5 μs on, 0.5 μs off repeating at 6.4 ms interval.)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

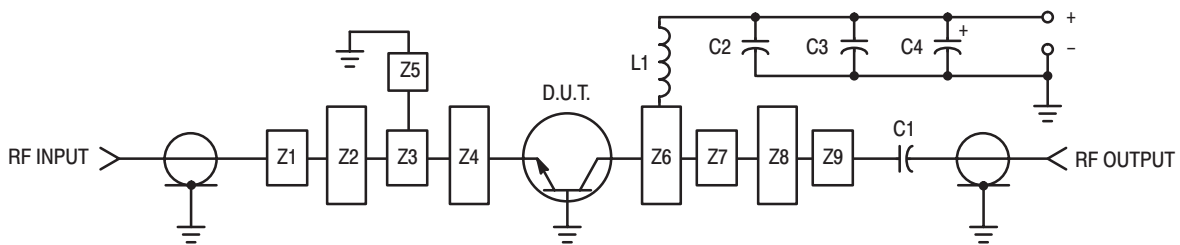
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	65	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	65	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 36 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	25	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20	—	—	—
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FUNCTIONAL TESTS

Common–Base Amplifier Power Gain ($V_{CC} = 50 \text{ Vdc}$, $P_{out} = 350 \text{ W Peak}$, $f = 1090 \text{ MHz}$)	G_{PB}	8.5	9.0	—	dB
Collector Efficiency ($V_{CC} = 50 \text{ Vdc}$, $P_{out} = 350 \text{ W Peak}$, $f = 1090 \text{ MHz}$)	η	40	—	—	%
Load Mismatch ($V_{CC} = 50 \text{ Vdc}$, $P_{out} = 350 \text{ W Peak}$, $f = 1090 \text{ MHz}$, $VSWR = 10:1$ All Phase Angles)	ψ	No Degradation in Output Power			



- C1 — 75 pF 100 Mil Chip Capacitor
- C2 — 39 pF 100 Mil Chip Capacitor
- C3 — 0.1 μF
- C4 — 100 μF , 100 Vdc, Electrolytic
- L1 — 3 Turns #18 AWG, 1/8" ID, 0.18 Long

- Z1–Z9 — Microstrip, See Details
- Board Material — Teflon, Glass Laminate
- Dielectric Thickness = 0.030"
- $\epsilon_r = 2.55$, 2 Oz. Copper

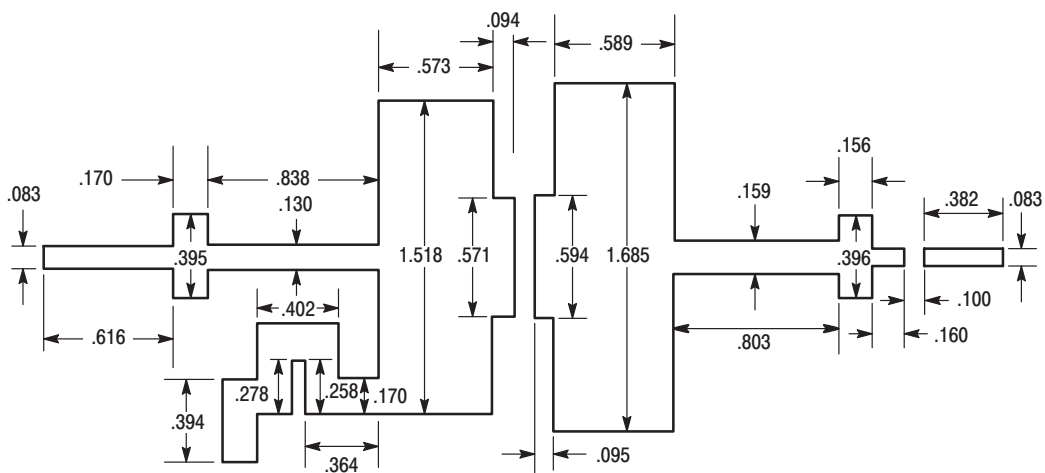
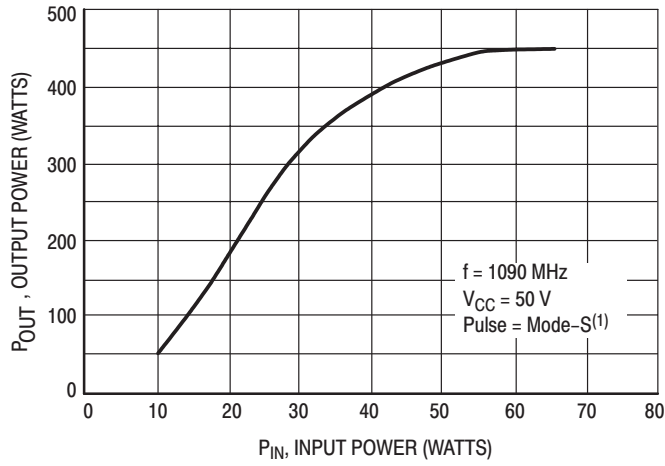
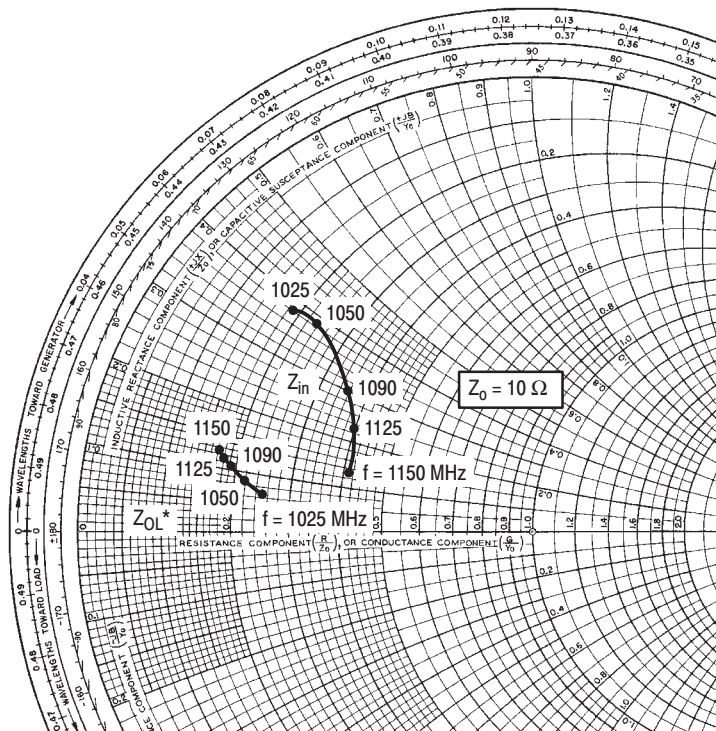


Figure 1. Test Circuit



(1) 128 μ s burst 0.5 μ s on, 0.5 μ s off repeating at 6.4 ms interval.

Figure 2. Output Power versus Input Power



$P_{OUT} = 350$ W Pk $V_{CC} = 50$ V

f MHz	Z_{in} OHMS	$Z_{OL}^* (1)$ OHMS
1025	$1.92 + j3.80$	$2.52 + j0.70$
1050	$2.44 + j3.92$	$2.18 + j0.85$
1090	$3.55 + j3.02$	$1.94 + j1.13$
1125	$4.11 + j2.27$	$1.80 + j1.22$
1150	$4.13 + j1.35$	$1.71 + j1.31$

Z_{OL}^* is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

